

FDMS86181E

MOSFET, N-Channel, Shielded Gate, POWERTRENCH®

100 V, 124 A, 4.2 mΩ

General Description

This N-Channel MV MOSFET is produced using ON Semiconductor's advanced POWERTRENCH® process that incorporates Shielded Gate technology. This process has been optimized to minimise on-state resistance and yet maintain superior switching performance with best in class soft body diode.

Features

- Shielded Gate MOSFET Technology
- Max $r_{DS(on)}$ = 4.2 mΩ at $V_{GS} = 10$ V, $I_D = 44$ A
- Max $r_{DS(on)}$ = 12 mΩ at $V_{GS} = 6$ V, $I_D = 22$ A
- ADD
- 50% lower Q_{rr} than other MOSFET suppliers
- Lowers switching noise/EMI
- MSL1 robust package design
- 100% UIL tested
- RoHS Compliant

Applications

- Primary DC-DC MOSFET
- Synchronous Rectifier in DC-DC and AC-DC
- Motor Drive
- Solar

MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

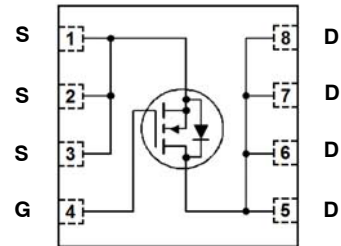
Symbol	Parameter	Value	Unit
V_{DS}	Drain to Source Voltage	100	V
V_{GS}	Gate to Source Voltage	±20	V
I_D	Drain Current:		A
	– Continuous $T_C = 25^\circ\text{C}$ (Note 5)	124	
	– Continuous $T_C = 100^\circ\text{C}$ (Note 5)	78	
	– Continuous $T_A = 25^\circ\text{C}$ (Note 1a)	17	
	– Pulsed (Note 4)	510	
E_{AS}	Single Pulse Avalanche Energy (Note 3)	337	mJ
P_D	Power Dissipation:		W
	$T_C = 25^\circ\text{C}$ $T_A = 25^\circ\text{C}$ (Note 1a)	125 2.5	
T_J, T_{STG}	Operating and Storage Junction Temperature Range	–55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

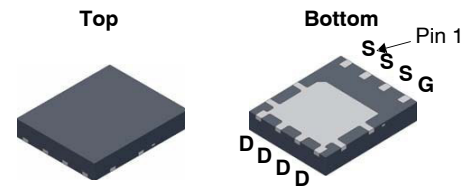


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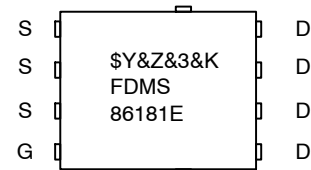


N-Channel MOSFET



Power 56
(PQFN8)
CASE 483AE

MARKING DIAGRAM



\$Y = ON Semiconductor Logo
 &Z = Assembly Plant Code
 &3 = Data Code (Year & Week)
 &K = Lot
 FDMS86181E = Specific Device Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

FDMS86181E

PACKAGE MARKING AND ORDERING INFORMATION

Device Marking	Device	Package	Quantity
FDMS86181E	FDMS86181E	Power 56 (PQFN8) (Pb-Free / Halogen Free)	3000/Tape&Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case	1.0	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	50	

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 250 \mu\text{A}$, $V_{GS} = 0 \text{ V}$	100			V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250 \mu\text{A}$, referenced to 25°C		60		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 80 \text{ V}$, $V_{GS} = 0 \text{ V}$			1	μA
I_{GSS}	Gate to Source Leakage Current, Forward	$V_{GS} = \pm 20 \text{ V}$, $V_{DS} = 0 \text{ V}$			100	nA

ON CHARACTERISTICS

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 250 \mu\text{A}$	2.0	3.1	4.0	V
$\Delta V_{GS(th)} / \Delta T_J$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250 \mu\text{A}$, referenced to 25°C		-9		mV/°C
$r_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10 \text{ V}$, $I_D = 44 \text{ A}$		3.3	4.2	m Ω
		$V_{GS} = 6 \text{ V}$, $I_D = 22 \text{ A}$		5.3	12	
		$V_{GS} = 10 \text{ V}$, $I_D = 44 \text{ A}$, $T_J = 125^\circ\text{C}$		5.7	7.8	
g_{FS}	Forward Transconductance	$V_{DS} = 10 \text{ V}$, $I_D = 44 \text{ A}$		116		S

DYNAMIC CHARACTERISTICS

C_{iss}	Input Capacitance	$V_{DS} = 50 \text{ V}$, $V_{GS} = 0 \text{ V}$, $f = 1 \text{ MHz}$		2945	4125	pF
C_{oss}	Output Capacitance			1730	2425	pF
C_{rss}	Reverse Transfer Capacitance			20	40	pF
R_g	Gate Resistance	$f = 1 \text{ MHz}$	0.1	1.3	2.6	Ω

SWITCHING CHARACTERISTICS

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 50 \text{ V}$, $I_D = 44 \text{ A}$, $V_{GS} = 10 \text{ V}$, $R_{GEN} = 6 \Omega$		17	31	ns
t_r	Rise Time			9	18	ns
$t_{d(off)}$	Turn-Off Delay Time			25	40	ns
t_f	Fall Time			6	12	ns
Q_g	Total Gate Charge	$V_{GS} = 0 \text{ V}$ to 10 V , $V_{DD} = 50 \text{ V}$, $I_D = 44 \text{ A}$		42	59	nC
		$V_{GS} = 0 \text{ V}$ to 6 V , $V_{DD} = 50 \text{ V}$, $I_D = 44 \text{ A}$		27	38	nC
Q_{gs}	Gate to Source Charge	$V_{DD} = 50 \text{ V}$, $I_D = 44 \text{ A}$		13		nC
Q_{gd}	Gate to Drain "Miller" Charge			9.3		nC

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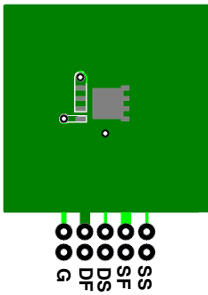
ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted) (continued)

Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
V_{SD}	Source to Drain Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 2.1\text{ A}$ (Note 2)		0.7	1.2	V
		$V_{GS} = 0\text{ V}, I_S = 44\text{ A}$ (Note 2)		0.8	1.3	
t_{rr}	Reverse Recovery Time	$I_F = 20\text{ A}, di/dt = 300\text{ A}/\mu\text{s}$		32	52	ns
Q_{rr}	Reverse Recovery Charge			57	92	
t_{rr}	Reverse Recovery Time	$I_F = 20\text{ A}, di/dt = 1000\text{ A}/\mu\text{s}$		25	40	ns
Q_{rr}	Reverse Recovery Charge			158	253	

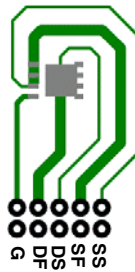
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

NOTES:

- $R_{\theta JA}$ is determined with the device mounted on a 1 in² pad 2 oz copper pad on a 1.5 × 1.5 in. board of FR-4 material. $R_{\theta CA}$ is determined by the user's board design.



a. 50 °C/W when mounted on a 1 in² pad of 2 oz copper.



b. 125 °C/W when mounted on a minimum pad of 2 oz copper.

- Pulse Test: Pulse Width < 300 μs , Duty cycle < 2.0%.
- E_{AS} of 337 mJ is based on starting $T_J = 25^\circ\text{C}$, N-ch: $L = 3\text{ mH}$, $I_{AS} = 15\text{ A}$, $V_{DD} = 100\text{ V}$, $V_{GS} = 10\text{ V}$. 100% test at $L = 0.1\text{ mH}$, $I_{AS} = 49\text{ A}$.
- Pulsed I_D please refer to Figure 11 SOA graph for more details.
- Computed continuous current limited to Max Junction Temperature only, actual continuous current will be limited by thermal & electro-mechanical application board design.

TYPICAL CHARACTERISTICS

($T_J = 25^\circ\text{C}$ unless otherwise noted)

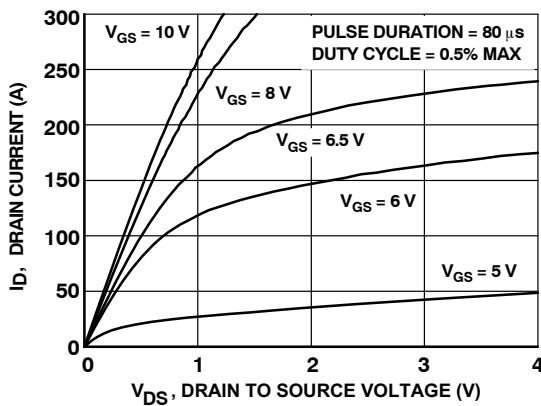


Figure 1. On Region Characteristics

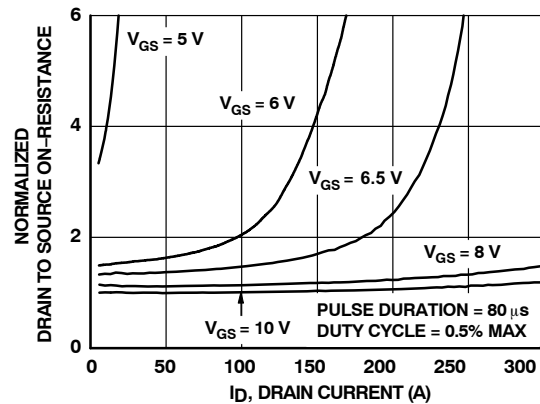


Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage

TYPICAL CHARACTERISTICS (continued)

($T_J = 25^\circ\text{C}$ unless otherwise noted)

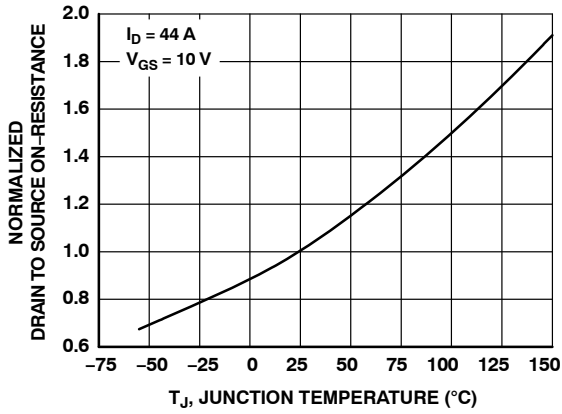


Figure 3. Normalized On Resistance vs. Junction Temperature

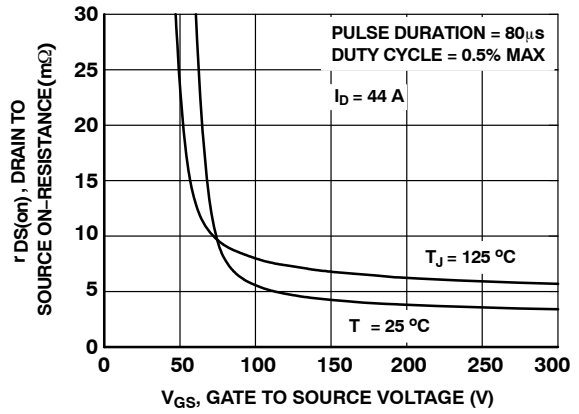


Figure 4. On-Resistance vs. Gate to Source Voltage

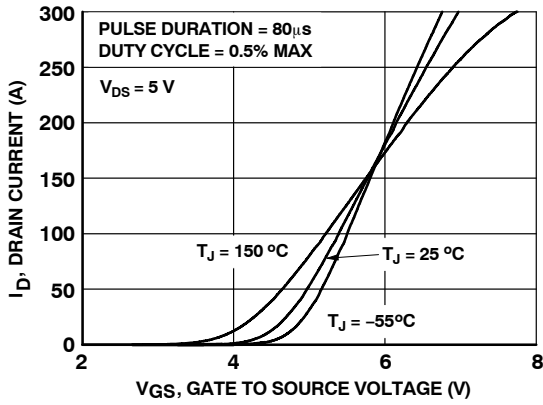


Figure 5. Transfer Characteristics

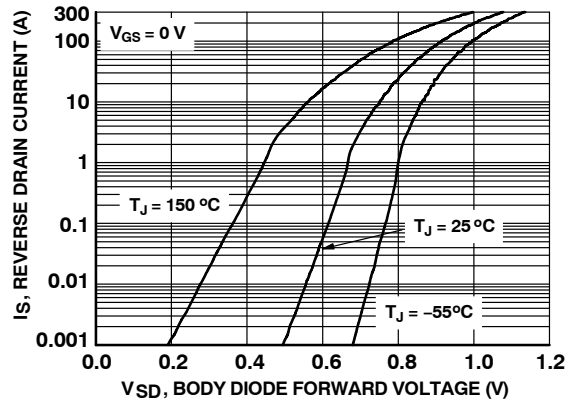


Figure 6. Source to Drain Diode Forward Voltage vs. Source Current

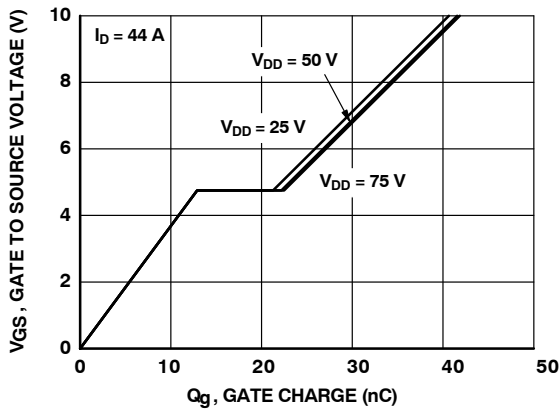


Figure 7. Gate Charge Characteristics

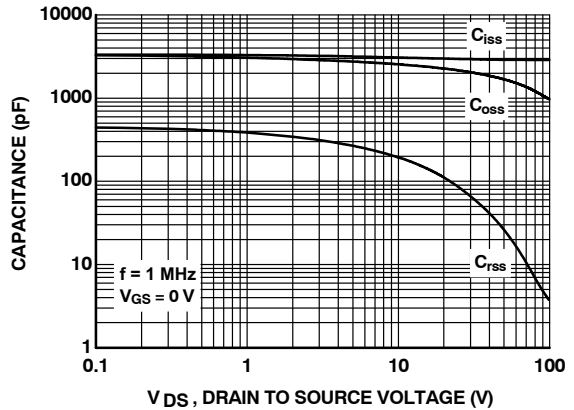


Figure 8. Capacitance vs. Drain to Source Voltage

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TYPICAL CHARACTERISTICS (continued)

($T_J = 25^\circ\text{C}$ unless otherwise noted)

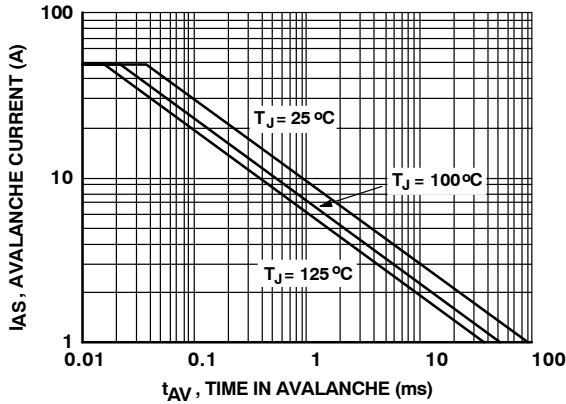


Figure 9. Unclamped Inductive Switching Capability

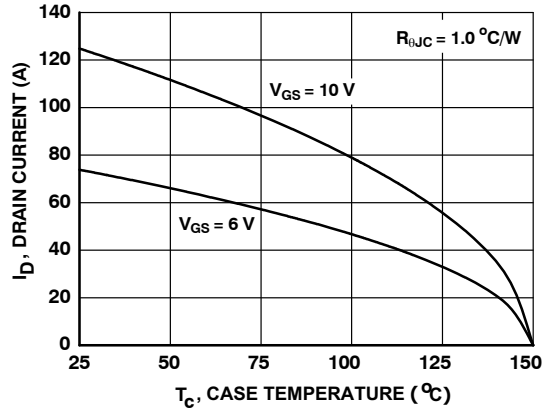


Figure 10. Maximum Continuous Drain Current vs. Case Temperature

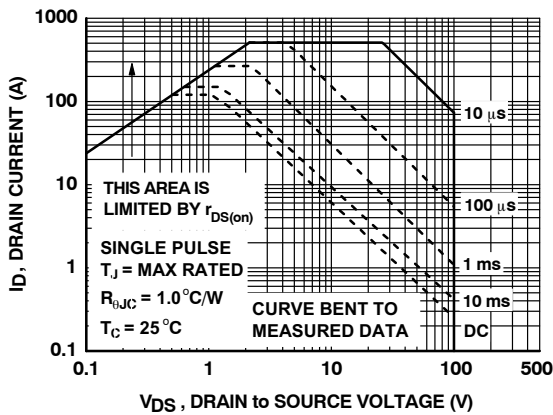


Figure 11. Forward Bias Safe Operating Area

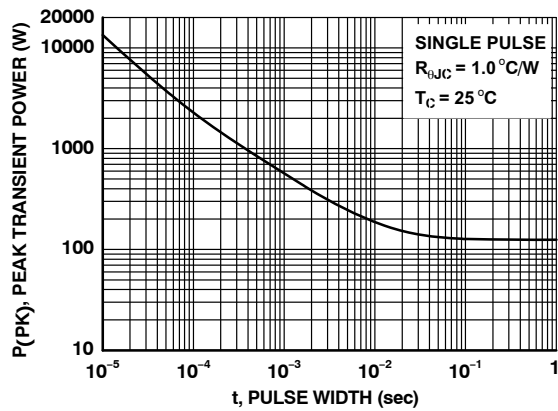


Figure 12. Single Pulse Maximum Power Dissipation

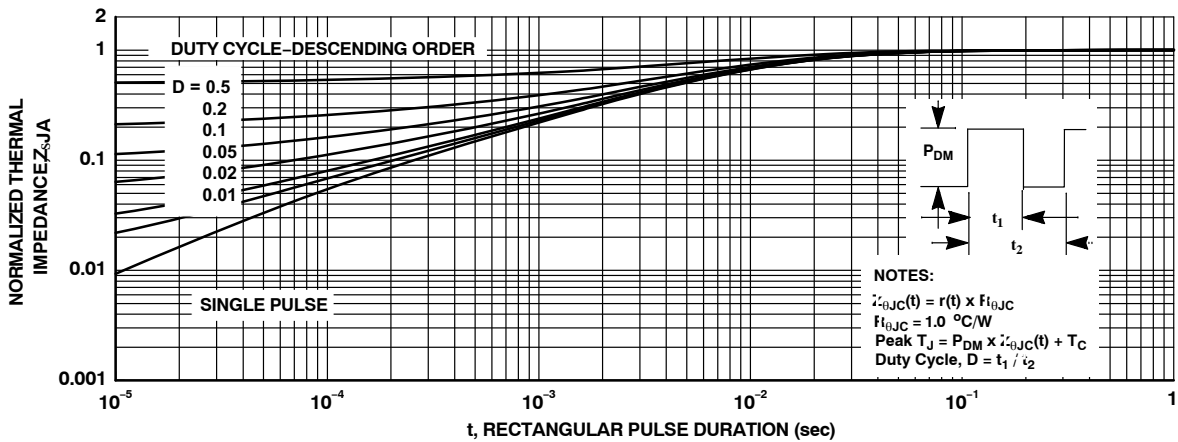
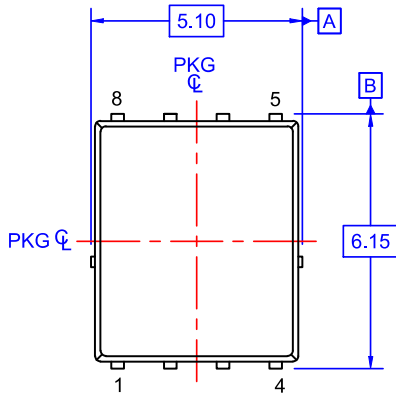


Figure 13. Transient Thermal Response Curve

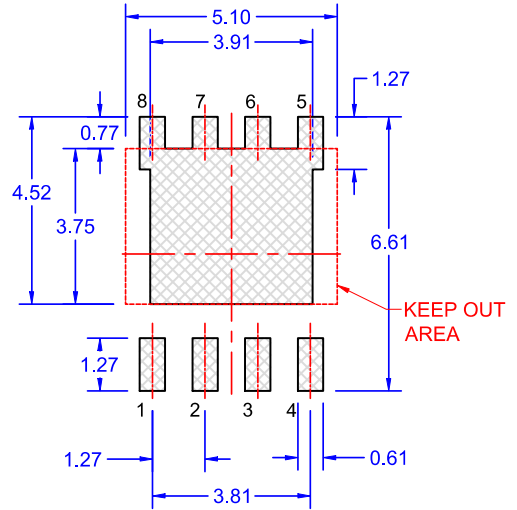
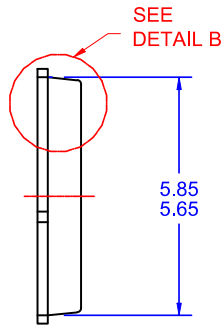
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PACKAGE DIMENSIONS

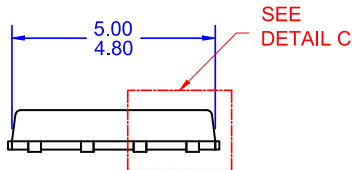
PQFN8 5X6, 1.27P
CASE 483AE
ISSUE A



TOP VIEW

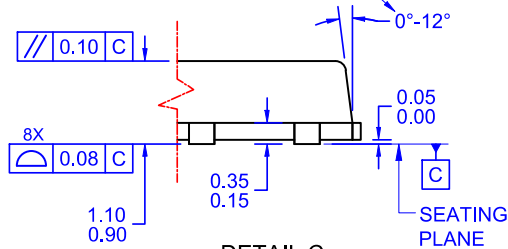


LAND PATTERN RECOMMENDATION

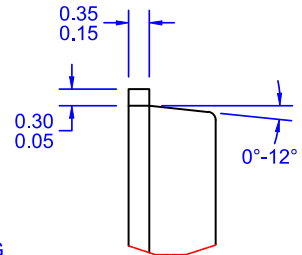


SIDE VIEW

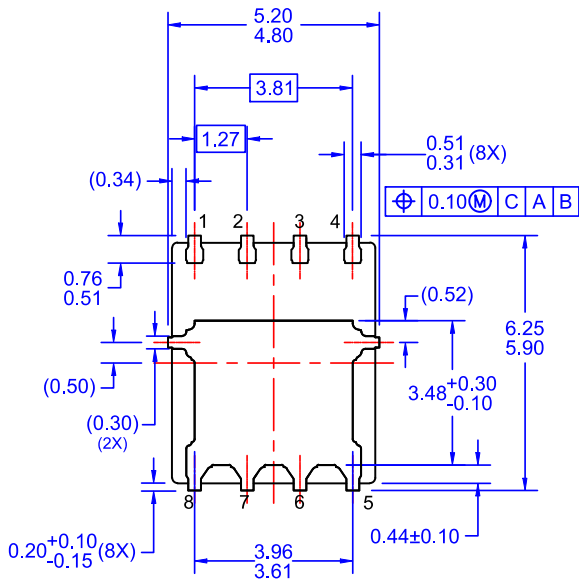
OPTIONAL DRAFT ANGLE MAY APPEAR ON FOUR SIDES OF THE PACKAGE



DETAIL C
SCALE: 2:1



DETAIL B
SCALE: 2:1




BOTTOM VIEW

NOTES: UNLESS OTHERWISE SPECIFIED

- A. PACKAGE STANDARD REFERENCE: JEDEC MO-240, ISSUE A, VAR. AA..
- B. DIMENSIONS DO NOT INCLUDE BURRS OR MOLD FLASH. MOLD FLASH OR BURRS DOES NOT EXCEED 0.10MM.
- C. ALL DIMENSIONS ARE IN MILLIMETERS.
- D. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-2009.
- E. IT IS RECOMMENDED TO HAVE NO TRACES OR VIAS WITHIN THE KEEP OUT AREA.

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